

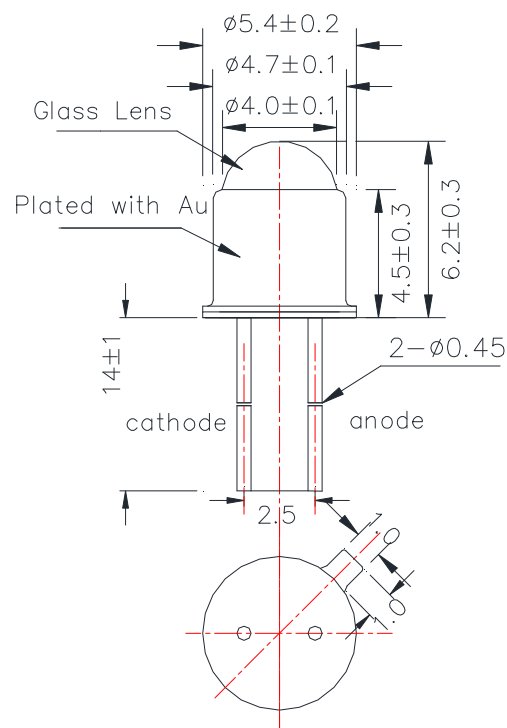
Data Sheet

L970-40M32

Stem type LED Lamp

USHIO

Outline and Internal Circuit



(Unit : mm)

Features

- Non-hermetic package
- Chip Material : GaAs
- Chip Dimension : 400um * 400um
- Number of Chips : 1pce
- Peak Wavelength : 970nm typ.
- Stem: TO-18 type
- Lens : Glass Ball Lens
- Cap : Gold Plated

Application

Absolute Maximum Ratings (Tc=25°C)

Item	Symbol	Ratings	Unit
Power Dissipation	PD	150	mW
Forward Current	IF	100	mA
Pulse Forward Current	IFP	1000	mA
Reverse Voltage	VR	5	V
Thermal Resistance	Rthja	300	K/W
Junction Temperature	Tj	120	°C
Operating Temperature	Topr	-40 ~ +100	°C
Storage Temperature	Tstg	-40 ~ +100	°C
Soldering Temperature	TSOL	250	°C

‡Pulse Forward Current condition : Duty 1% and Pulse Width=10us.

‡Soldering condition: Soldering condition must be completed within 5 seconds at 250°C and is allowed in the area apart 3mm from the bottom of the lamp.

Optical and Electrical Characteristics (Tc=25°C)

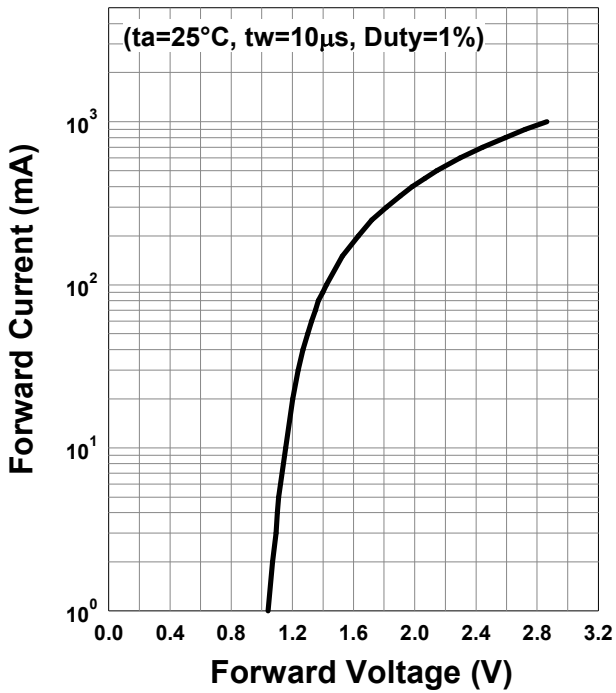
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Forward Voltage	VF		1.3	1.5	V	IF=50mA
	VFP		2.9			IFP=1A
Total Radiated Power	PO		6.5		mW	IF=50mA
			98			IFP=1A
Radiant Intensity	IE		18		mW/sr	IF=50mA
			270			IFP=1A
Peak Wavelength	λ_p	955		975	nm	IF=50mA
Half Width	$\Delta\lambda$		48		nm	IF=50mA
Viewing Half Angle	$\theta_{1/2}$		± 16		deg.	IF=50mA
Rise Time	tr		200		ns	IF=50mA
Fall Time	tf		500		ns	IF=50mA

‡ Radiated Power is measured by S3584-08.

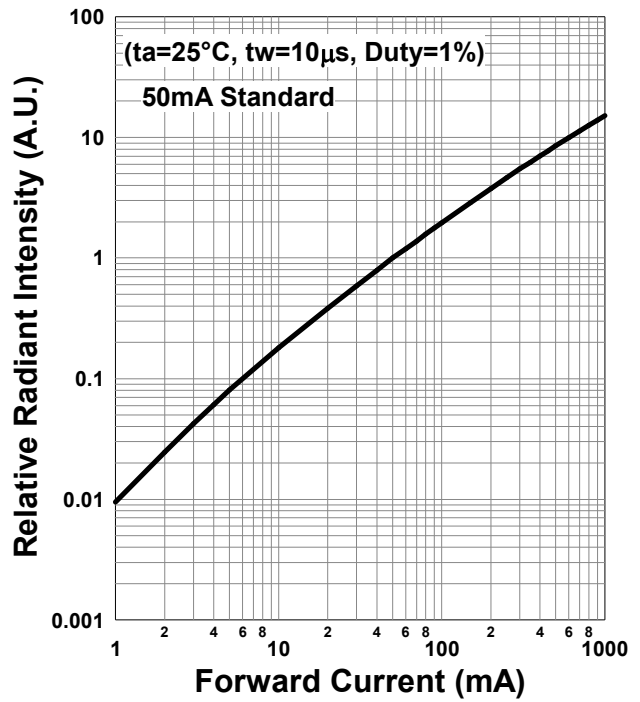
‡ Radiant Intensity is measured by CIE127-2007 Condition B.

Typical Characteristic Curves

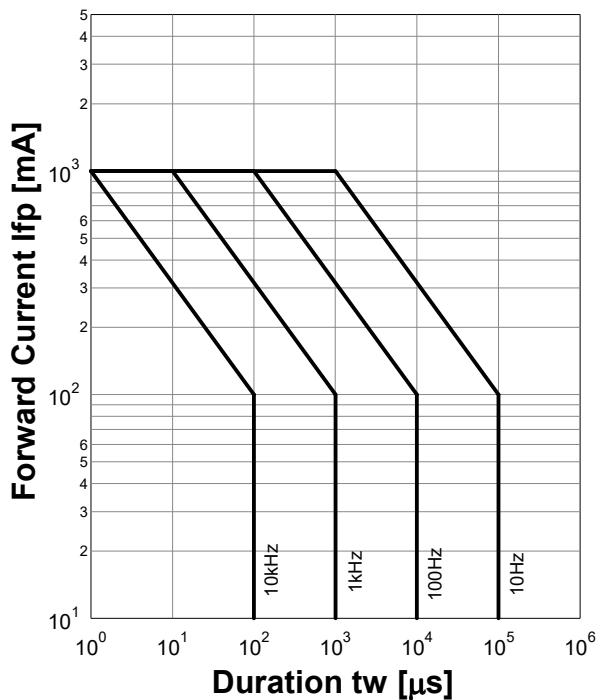
Forward Current - Forward Voltage



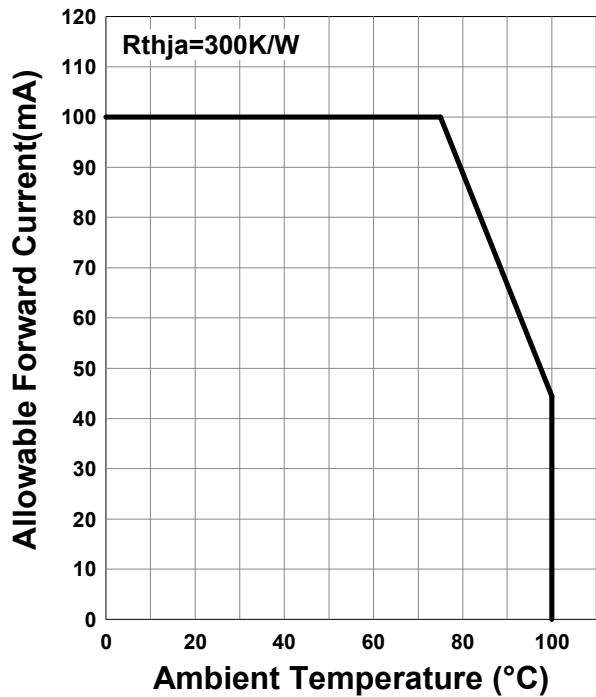
Relative Radiant Intensity - Forward Current



Forward Current - Pulse Duration

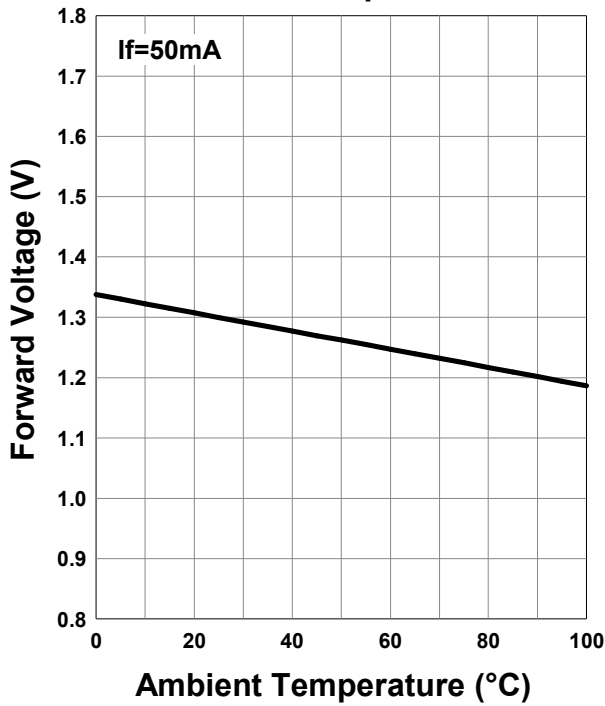


Allowable Forward Current - Ambient Temperature

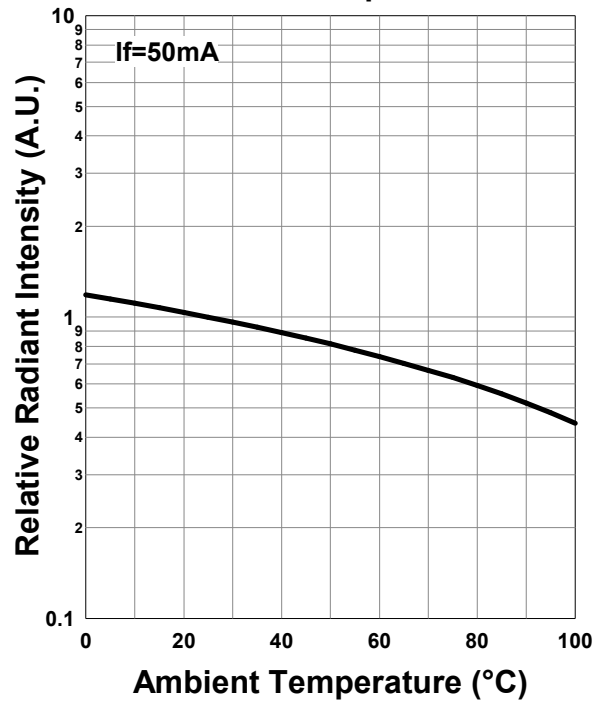


Data Sheet L970-40M32

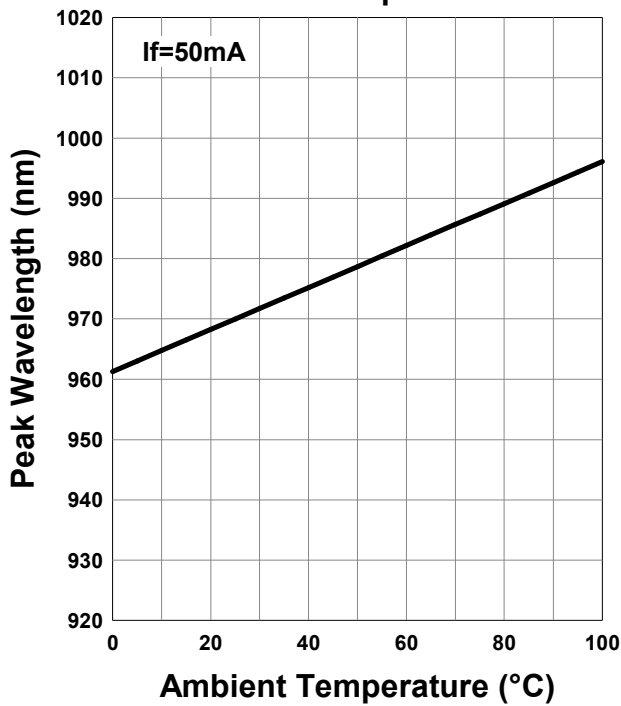
Forward Voltage - Ambient Temperature



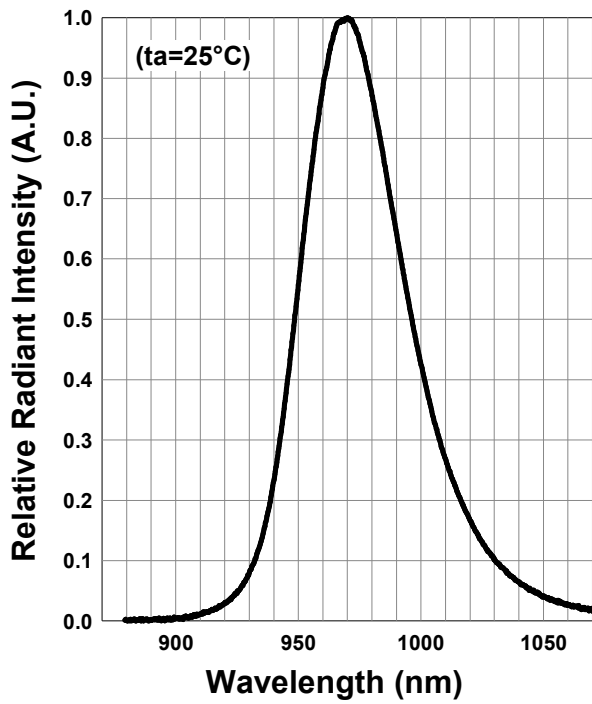
Relative Radiant Intensity - Ambient Temperature



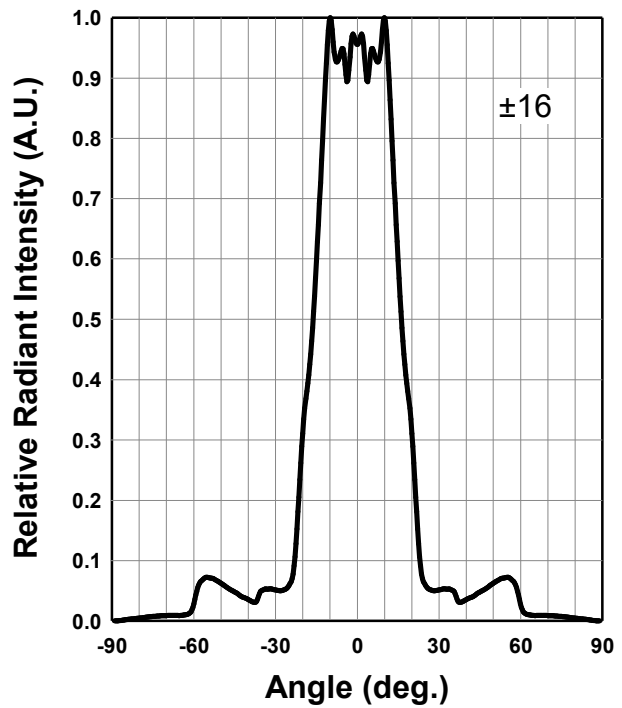
Peak Wavelength - Ambient Temperature



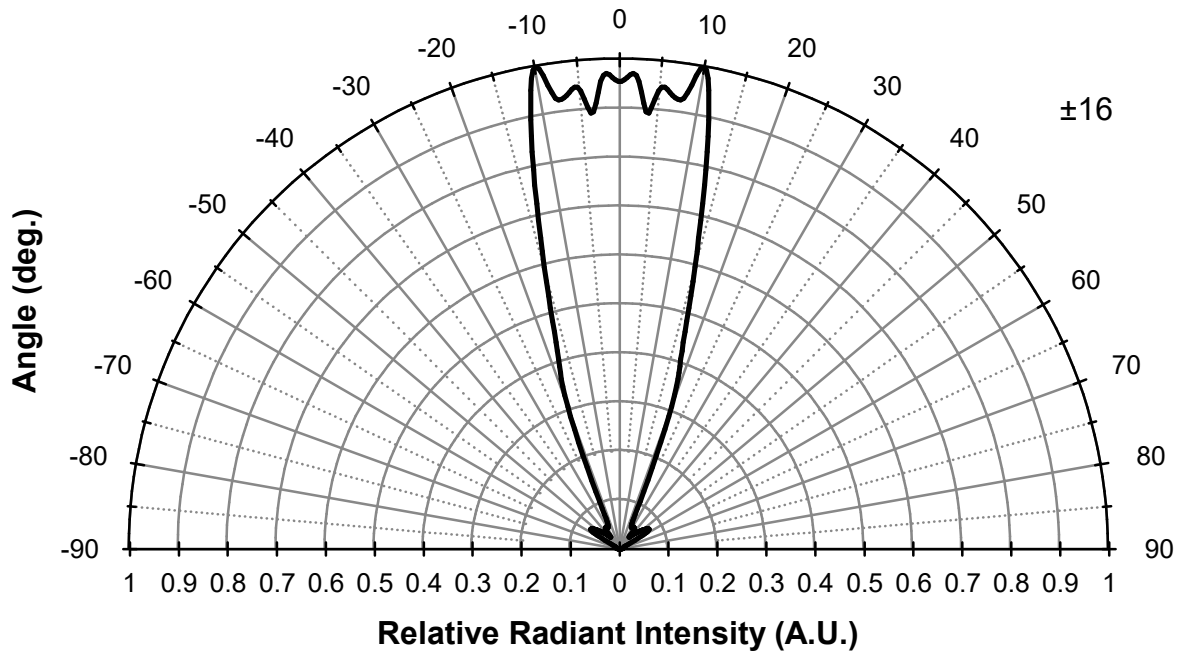
Relative Spectral Emission



Radiation Characteristics



Radiation Characteristics



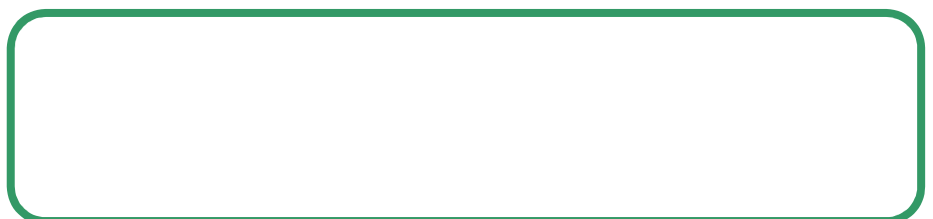
Disclaimer

Product specifications and data shown in this product catalog are subject to change without notice for the purposes of improving product performance, reliability, design, or otherwise.

Product data and parameters in this catalog are typical values based on reasonably up-to-date measurements.

Product data and parameters may vary by user application and over time.

Products shown in this catalog are intended to be used for general electronic equipment. Products are not guaranteed for applications where product malfunction or failure may cause personal injury or death, including but not limited to life-supporting / saving devices, medical devices, safety devices, airplanes, aerospace equipment, automobiles, traffic control systems, and nuclear reactor control systems.



*Effective July 2016, Ushio Epitex Inc. is now USHIO OPTO SEMICONDUCTORS, INC.